

## Small Signal Switching Chip Diode Dual Series

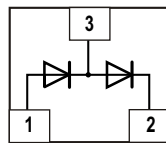
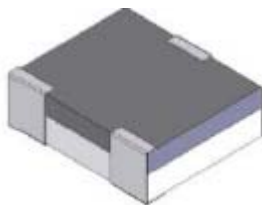
REVERSE VOLTAGE - 100 Volts  
FORWARD CURRENT - 0.2 Ampere

### FEATURES

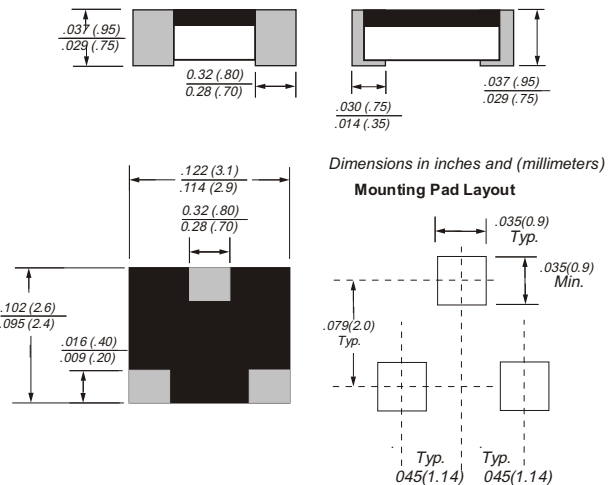
- Silicon Epitaxial Planar Chip Diode.
- Fast Switching dual chip diode with anode to cathode.
- Green product

### MECHANICAL DATA

- Case : SIT23CD Plastic case
- Weight : approx 21 grams



### SOT-23CD



### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.  
Single phase, half wave, 60Hz, resistive or inductive load.  
For capacitive load, derate current by 20%

PARAMETER	SYMBOL	BAV99	UNIT
Non repetitive peak reverse voltage	VRM	100	V
Repetitive peak reverse voltage	VR=VRRM	70	V
Forward continuous current	IF	200	mA
Average forward current	IFAV	150	mA
Non repetitive peak forward current	IFSM	2.0	A
tp=1uS		1.0	
tp=1mS		0.5	
Forward voltage	VF	715	mV
IF=1mA		855	
IF=10mA		1000	
IF=50mA		1250	
Leakage current	IR	2.5	uA
@70V@25°C		50	
@70V@125°C		30	
Power dissipation	Ptot	300	mW
Reverse recovery time (IF=10mA to IR=1mA, VR=6V, RL=100Ω)	Trr	4	nS
Diode capacitance (VF=VR=0, F=1MHZ)	Ctot	4	pF
Thermal resistance junction to ambient air	RθJA	430	K/W
Operating Temperature Range	TJ	-55 to +150	°C
Storage Temperature Range	TSTG	-55 to +150	°C

## Typical Characteristics

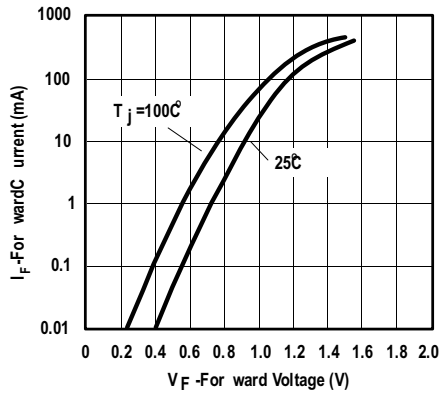


Figure1. Forward Current vs. Forward Voltage

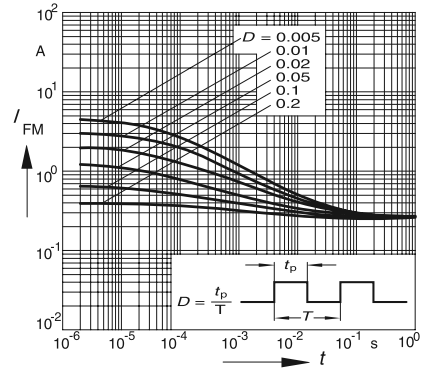


Figure2. Peak forward current  $I_{FM} = f(t_p)$

## Device outlook

Kunshan plant (front side)



Kunshan plant (back side)



### Suggested thermal profiles for soldering processes

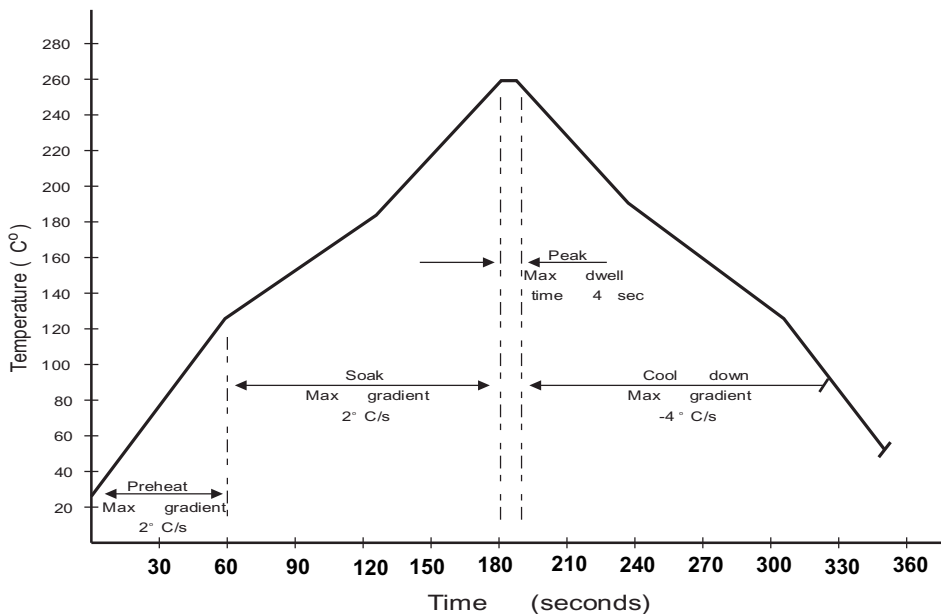


Fig.1 Typical Wave Soldering Thermal Profile

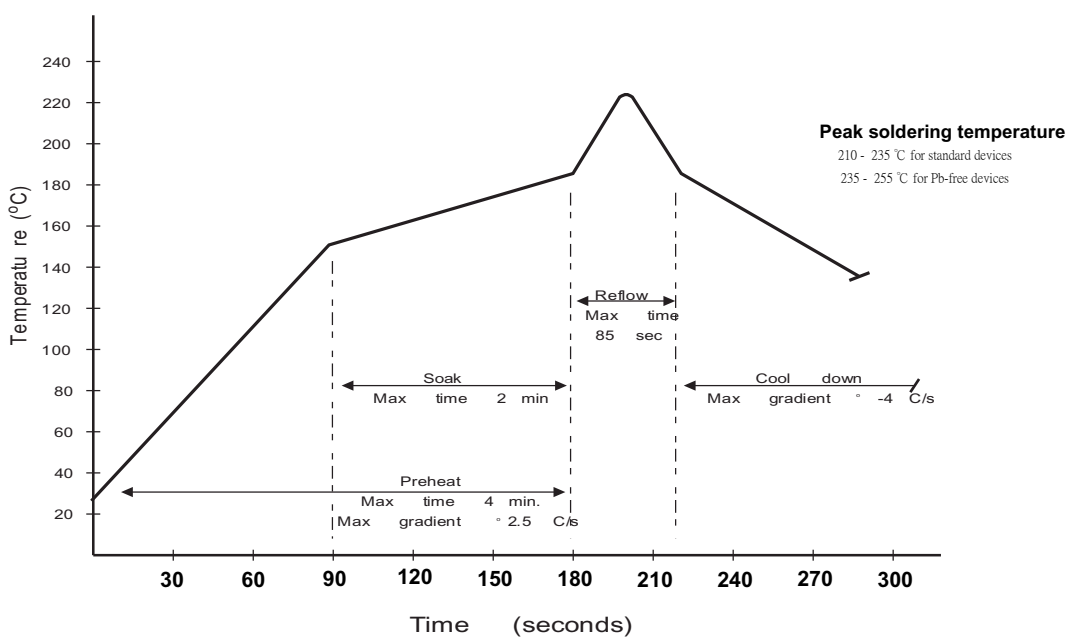


Fig2. Typical IR Reflow Soldering Thermal Profile